

external supply voltage to an internal supply voltage lower than said external supply voltage within said chip;

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wherein, when said external supply voltage is not higher than a predetermined first voltage, the output voltage of said voltage limiter means increases at a rate which is substantially equal to the increasing rate of said external supply voltage, when said external supply voltage is between a level exceeding said first voltage and a predetermined second voltage, said output voltage increases at a rate which is lower than the increasing rate of said external supply voltage, and after said external supply voltage exceeds said second voltage, said internal supply voltage increases at a rate which is higher than the increasing rate thereof when said external supply voltage is between a level exceeding said first voltage and said second voltage.

8. A semiconductor integrated circuit according to claim 7, wherein said internal supply voltage is set so that a stress voltage condition of transistors included in said first circuits is substantially equal to that of transistors included in said second circuits.

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9. A semiconductor integrated circuit according to claim 7, wherein the change of said internal supply voltage is made inside said voltage limiter means by detecting a change in said external supply voltage. on

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10. A semiconductor integrated circuit according to claim 9,  
wherein said external supply voltage is between a level  
exceeding said first voltage and said second voltage when said  
semiconductor integrated circuit is in a normal operative state,  
and said external supply voltage exceeds said second voltage when  
said semiconductor integrated circuit is in an aging state.

11. A semiconductor integrated circuit according to claim <sup>3</sup>10,  
wherein the <sup>third</sup> rate of change of said internal supply voltage when  
said external supply voltage is between a level exceeding said  
second voltage and a predetermined third voltage is <sup>larger</sup> higher than  
<sup>a fourth</sup> the rate of change of said internal supply voltage after said  
external supply voltage exceeds said third voltage.

12. A semiconductor integrated circuit according to claim 11,  
wherein, when said external supply voltage is between said first  
voltage and said second voltage, <sup>the magnitude of</sup> said internal supply voltage is  
substantially constant.

13. A semiconductor integrated circuit comprising:  
a chip;  
load circuits provided on said chip; and  
a voltage limiter means provided on said chip for reducing  
an external supply voltage to an internal supply voltage lower

than said external supply voltage within said chip and supplying it to said load circuits;

wherein the internal supply voltage is output from said voltage limiter means in response to the operation of said load circuits by controlling a signal for controlling said voltage limiter means and a signal for controlling said load circuits.

14. A semiconductor integrated circuit according to claim 13, wherein said internal supply voltage is set so that a stress voltage condition of transistors constituting said load circuits is substantially equal to that of transistors constituting said voltage limiter means.

15. A semiconductor integrated circuit according to claim 14, wherein the change of said internal supply voltage is made inside said ~~voltage limiter~~ <sup>internal power supply</sup> means by detecting a change in said external supply voltage.

16. A semiconductor integrated circuit according to claim 15, wherein, when said external supply voltage is not higher than a predetermined first voltage, the output voltage of said voltage limiter means increases at a rate which is substantially equal to the increasing rate of said external supply voltage, when said external supply voltage is between a level exceeding said first voltage and a predetermined second voltage, said output voltage increases at a rate which is lower than the increasing rate of

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said external supply voltage, and after said external supply voltage exceeds said second voltage, said internal supply voltage increases at a rate which is higher than the increasing rate thereof when said external supply voltage is between a level exceeding said first voltage and said second voltage.

17. A semiconductor integrated circuit according to claim 16, wherein said external supply voltage is between a level exceeding said first voltage and said second voltage when said semiconductor integrated circuit is in a normal operative state, and said external supply voltage exceeds said second voltage when said semiconductor integrated circuit is in an aging state.

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18. A semiconductor integrated circuit according to claim <sup>8</sup> 17, wherein the <sup>third</sup> rate of change of said internal supply voltage when said external supply voltage is between a level exceeding said second voltage and a predetermined third voltage is <sup>larger</sup> higher than <sup>a fourth</sup> the rate of change of said internal supply voltage after said external supply voltage exceeds said third voltage.

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19. A semiconductor integrated circuit according to claim 18, wherein, when said external supply voltage is between said first voltage and said second voltage, <sup>the magnitude of</sup> said internal supply voltage is substantially constant.